AMENDMENTS TO THE CLAIMS

This listing of claims replaces all prior versions of claims in the application.

1. (Currently Amended): A semiconductor device fabrication method comprising ~~the steps of~~:

polishing a surface of a film-to-be-polished formed over a semiconductor substrate with a polishing pad while only a polishing slurry is supplied onto the polishing pad to [[thereby]] planarize the surface of the film-to-be-polished; and

after the surface of the film-to-be-polished has been planarized, further polishing the surface of the film-to-be-polished with [[the]] a polishing pad while said polishing slurry and water are supplied onto the polishing pad, said polishing slurry and said water being supplied onto the polishing pad separately,

wherein said polishing slurry comprises abrasive grains and a surfactant additive, and

wherein in the further polishing the surface of the film-to-be-polished, said polishing slurry is supplied onto the polishing pad through a nozzle, and said water is supplied onto the polishing pad through another nozzle.

2. (Currently Amended): A semiconductor device fabrication method comprising ~~the steps of~~:

polishing a surface of a film-to-be-polished formed over a semiconductor substrate with a polishing pad while only a polishing slurry is supplied onto the polishing pad to [[thereby]] planarize the surface of the film-to-be-polished; and

after the surface of the film-to-be-polished has been planarized, further polishing the surface of the film-to-be-polished with [[the]] a polishing pad while a mixture of said polishing slurry and water is supplied onto the polishing pad,

wherein said polishing slurry comprises abrasive grains and a surfactant additive, [[and]]

wherein a water content in said mixture of said polishing slurry and said water is higher than a water content in said polishing slurry, and

wherein in the further polishing the surface of the film-to-be-polished, said mixture of said polishing slurry and said water is supplied onto the polishing pad through a nozzle.

3. (Currently Amended): A semiconductor device fabrication method comprising ~~the steps of~~:

polishing a surface of a film-to-be-polished formed over a semiconductor substrate with a polishing pad while only a polishing slurry is supplied onto the polishing pad to [[thereby]] planarize the surface of the film-to-be-polished; and

after the surface of the film-to-be-polished has been planarized, further polishing the surface of the film-to-be-polished with [[the]] a polishing pad while said polishing slurry and water are supplied onto the polishing pad, said polishing slurry and said water being supplied onto the polishing pad separately,

wherein said polishing slurry comprises abrasive grains and a surfactant additive, [[and]]

wherein in the ~~step of~~ further polishing the surface of the film-to-be-polished, the water is supplied to a position outer of a position for said polishing slurry to be supplied to, and

wherein in the further polishing the surface of the film-to-be-polished, said polishing slurry is supplied onto the polishing pad through a nozzle, and said water is supplied onto the polishing pad through another nozzle.

4. (Currently Amended): A semiconductor device fabrication method comprising ~~the steps of~~:

polishing a surface of a film-to-be-polished formed over a semiconductor substrate with a polishing pad while only a polishing slurry is supplied onto the polishing pad to [[thereby]] planarize the surface of the film-to-be-polished; and

after the surface of the film-to-be-polished has been planarized, further polishing the surface of the film-to-be-polished with [[the]] a polishing pad while said polishing slurry and water are supplied onto the polishing pad, said polishing slurry and said water being supplied onto the polishing pad separately,

wherein said polishing slurry comprises abrasive grains and a surfactant additive, [[and]]

wherein in the ~~step of~~ further polishing the surface of the film-to-be-polished, a supply amount of [[the]] said water is 2 or more times as much as a supply amount of said polishing slurry, and

wherein in the further polishing the surface of the film-to-be-polished, said polishing slurry is supplied onto the polishing pad through a nozzle, and said water is supplied onto the polishing pad through another nozzle.

5-11 (Cancelled).

12. (Currently Amended): A semiconductor device fabrication method according to claim 1, further comprising, before the ~~step of~~ planarizing the surface of the film-to-be-polished~~, the steps of~~:

forming over the semiconductor substrate an insulation film having polish characteristics different from those of the film-to-be-polished;

forming an opening in the insulation film;

etching the semiconductor substrate with the insulation film as a mask to form a trench in the semiconductor substrate; and

forming the film-to-be-polished in the trench and over the insulation film,

in the ~~step of~~ further polishing the surface of the film-to-be-polished, the surface of the film-to-be-polished is polished with the insulation film as a stopper.

13. (Currently Amended): A semiconductor device fabrication method according to claim 2, further comprising, before the ~~step of~~ planarizing the surface of the film-to-be-polished~~, the steps of~~:

forming over the semiconductor substrate an insulation film having polish characteristics different from those of the film-to-be-polished;

forming an opening in the insulation film;

etching the semiconductor substrate with the insulation film as a mask to form a trench in

the semiconductor substrate; and

forming the film-to-be-polished in the trench and over the insulation film,

in the ~~step of~~ further polishing the surface of the film-to-be-polished, the surface of the film-to-be-polished is polished with the insulation film as a stopper.

14-27 (Cancelled).

28. (Original): A semiconductor device fabrication method according to claim 1, wherein

the abrasive grains comprise cerium oxide or silicon oxide,

the additive comprises poly(ammonium acrylate).

29. (Original): A semiconductor device fabrication method according to claim 2, wherein

the abrasive grains comprise cerium oxide or silicon oxide,

the additive comprises poly(ammonium acrylate).

30-33 (Cancelled).

34. (Currently Amended): A semiconductor device fabrication method according to claim 1, wherein

in the ~~step of~~ further polishing the surface of the film-to-be-polished, a supply amount of said polishing slurry to a supply amount of said water is 1:5.

35. (New): A semiconductor device fabrication method according to claim 1, wherein the polishing pad used in the further polishing the surface of the film-to-be-polished is different from the polishing pad used in the polishing the surface of the film-to-be-polished to planarize the surface of the film-to-be-polished.

36. (New): A semiconductor device fabrication method according to claim 2, wherein the polishing pad used in the further polishing the surface of the film-to-be-polished is different from the polishing pad used in the polishing the surface of the film-to-be-polished to planarize the surface of the film-to-be-polished.